

Practitioner's Docket No. MI22-1171

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Akram et al., Salman

Application No.: 09/292,132

Filed: 04/14/99

For: Methods of Forming a Transistor Gate

Group No.: 2812

Examiner: S. Mulpuri

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Response to November 6, 2003 Office Action

December 8, 2003
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. 09/292,132
Filing Date April 14, 1999
Inventor Salman Akram et al.
Assignee Micron Technology, Inc.
Group Art Unit 2812
Examiner S. Mulpuri
Attorney's Docket No. MI22-1171
Title: Methods of Forming A Transistor Gate

RESPONSE TO NOVEMBER 6, 2003 OFFICE ACTION

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Responsive to the Office Action dated November, 2003, Applicant amends
and remarks as follows:

AMENDMENTS

Underlines indicate insertions and ~~strikeouts~~ indicate deletions.